

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	29	electrode with "Si.sub.3" adj "N.sub.4" same chamber	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/03 15:45
L2	1	L1 and ((phase adj change) or chalcogenide)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/03 15:45
L3	1672	electrode with "Si.sub.3" adj "N.sub.4"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/03 15:45
L4	589	L3 and etch\$4 with "Si.sub.3" adj "N.sub.4"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/03 15:45
L5	180	L3 and etch\$4 with "Si.sub.3" adj "N.sub.4" with (pore or hole or trench or via or opening)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/03 15:45

EAST Search History

L6	0	L5 and (chalcogenide or phase adj change) with (pore or hole or trench or via or opening)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L7	0	L5 and ((chalcogenide or (phase adj change)) with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L8	7	L4 and ((chalcogenide or (phase adj change)) with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L9	11	L4 and ((chalcogenide or (phase adj change) or memory adj material) with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:49
L10	2	("5847442" "6204139").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/09/03 15:45
L11	3	("6583003").URPN.	USPAT	OR	OFF	2007/09/03 15:45
L12	3	("6204139" "6569745" "6583003").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/09/03 15:45

EAST Search History

L13	2	electrode with "Si.sub.3" adj "N.sub.4" with in adj situ	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L14	1672	electrode with "Si.sub.3" adj "N.sub.4"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L15	20	L14 and chalcogenide	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L16	11	L4 and ((chalcogenide or (phase adj change) or (memory adj material) or "GST" or "GeSbTe") with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L17	6	"6635951"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45

EAST Search History

L18	17	"6638820"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L19	56	"6153890"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L20	0	electrode with (silicon adj nitride) with in adj situ	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L21	289	electrode with (silicon adj nitride) with chamber	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L22	0	L21 and chalcogenide	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45

EAST Search History

L23	2028	L1 L2 L3 L4 L5 L6 L7 L8 L9 L10 L11 L12 L13 L14 L15 L16 L17 L18 L19 L20 L21 L22	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:45
L24	18980	vent\$4 with atmosphere with chamber	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:55
L25	18	24 and chalcogenide	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:49
L26	3	24 and ((chalcogenide or (phase adj change) or memory adj material) with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:54
L27	943	438/200.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:53

EAST Search History

L28	995	438/652.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:53
L29	8	27 and ((chalcogenide or (phase adj change) or memory adj material) with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:54
L30	9	28 and ((chalcogenide or (phase adj change) or memory adj material) with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:54
L31	1	29 and vent\$4 with atmosphere with chamber	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:55
L32	1	30 and vent\$4 with atmosphere with chamber	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/09/03 15:55

EAST Search History

S1	29	electrode with "Si.sub.3" adj "N.sub.4" same chamber	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:03
S2	1	S1 and ((phase adj change) or chalcogenide)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:02
S3	1671	electrode with "Si.sub.3" adj "N.sub.4"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:24
S4	589	S3 and etch\$4 with "Si.sub.3" adj "N.sub.4"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:03
S5	180	S3 and etch\$4 with "Si.sub.3" adj "N.sub.4" with (pore or hole or trench or via or opening)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:04

EAST Search History

S6	0	S5 and (chalcogenide or phase adj change) with (pore or hole or trench or via or opening)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:04
S7	0	S5 and ((chalcogenide or (phase adj change)) with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:05
S8	7	S4 and ((chalcogenide or (phase adj change)) with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:14
S9	11	S4 and ((chalcogenide or (phase adj change) or memory adj material) with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:29
S10	2	("5847442" "6204139").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 00:16
S11	1	("6583003").URPN.	USPAT	OR	OFF	2007/04/02 00:17
S12	3	("6204139" "6569745" "6583003").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 00:24

EAST Search History

S13	2	electrode with "Si.sub.3" adj "N.sub.4" with in adj situ	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:26
S14	1671	electrode with "Si.sub.3" adj "N.sub.4"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:26
S15	20	S14 and chalcogenide	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:26
S16	11	S4 and ((chalcogenide or (phase adj change) or (memory adj material) or "GST" or "GeSbTe") with (pore or hole or trench or via or opening))	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:55
S17	6	"6635951"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 00:35

EAST Search History

S18	16	"6638820"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 07:54
S19	52	"6153890"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 07:55
S20	0	electrode with (silicon adj nitride) with in adj situ	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 07:57
S21	277	electrode with (silicon adj nitride) with chamber	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 07:57
S22	0	S21 and chalcogenide	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 07:57